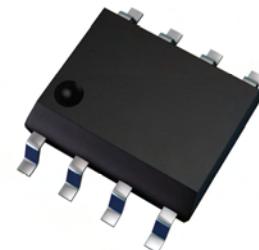


## ZXMHC6A07N8

### 60V SO8 Complementary enhancement mode MOSFET H-Bridge

#### Summary

Device	$V_{(BR)DSS}$	$Q_G$	$R_{DS(on)}$	$I_D$ $T_A = 25^\circ C$
N-CH	60V	3.2nC	0.25Ω @ $V_{GS} = 10V$	1.8A
			0.35Ω @ $V_{GS} = 4.5V$	1.5A
P-CH	-60V	5.1nC	0.40Ω @ $V_{GS} = -10V$	-1.4A
			0.60Ω @ $V_{GS} = -4.5V$	-1.2A



#### Description

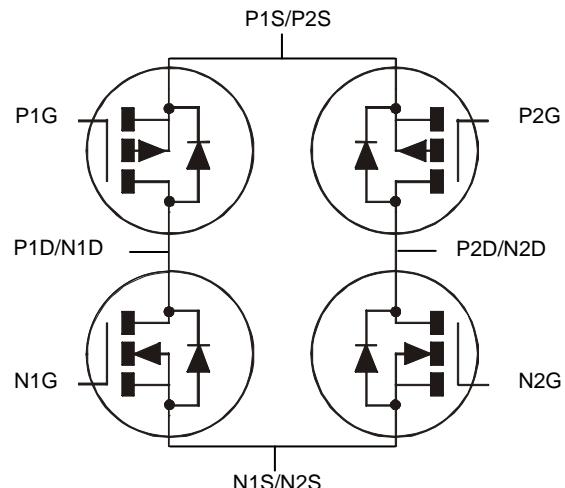
This new generation complementary MOSFET H-Bridge features low on-resistance achievable with low gate drive.

#### Features

- 2 x N + 2 x P channels in a SOIC package

#### Applications

- DC Motor control
- DC-AC Inverters

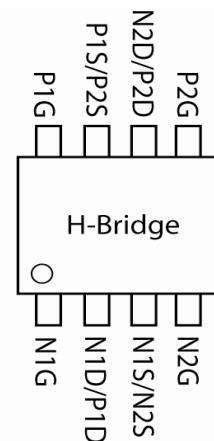


#### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMHC6A07N8TC	13	12	2,500

#### Device marking

ZXMHC  
6A07



**Absolute maximum ratings**

Parameter	Symbol	N-channel	P-channel	Unit
Drain-Source voltage	$V_{DSS}$	60	-60	V
Gate-Source voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain current @ $V_{GS} = 10V$ ; $T_A = 25^\circ C$ @ $V_{GS} = 10V$ ; $T_A = 70^\circ C$ @ $V_{GS} = 10V$ ; $T_A = 25^\circ C$ @ $V_{GS} = 10V$ ; $T_L = 25^\circ C$	$I_D$	1.80 1.40 1.39 1.42	-1.42 -1.28 -1.28 -1.33	A
Pulsed Drain current @ $V_{GS} = 10V$ ; $T_A = 25^\circ C$	$I_{DM}$	7.10	-6.03	A
Continuous Source current (Body diode) at $T_A = 25^\circ C$	$I_S$	1.00	-1.00	A
Pulsed Source current (Body diode) at $T_A = 25^\circ C$	$I_{SM}$	7.10	-6.03	A
Power dissipation at $T_A = 25^\circ C$ Linear derating factor	$P_D$	0.87 6.94		W mW/°C
Power dissipation at $T_A = 25^\circ C$ Linear derating factor	$P_D$	1.36 10.9		W mW/°C
Power dissipation at $T_L = 25^\circ C$ Linear derating factor	$P_D$	0.90 7.19		W mW/°C
Operating and storage temperature range	$T_j, T_{stg}$	-55 to 150		°C

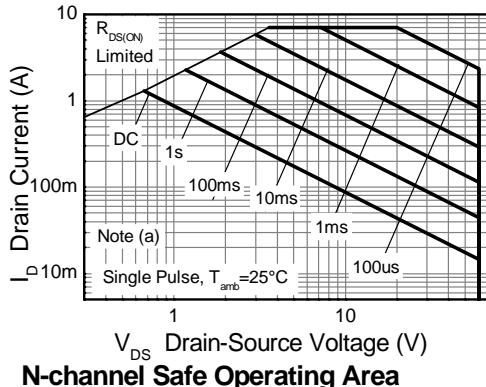
**Thermal resistance**

Parameter	Symbol	Value	Unit
Junction to ambient (a)	$R_{\theta JA}$	144	°C/W
Junction to ambient (b)	$R_{\theta JA}$	92	°C/W
Junction to ambient (d)	$R_{\theta JA}$	106	°C/W
Junction to ambient (e)	$R_{\theta JA}$	254	°C/W
Junction to lead (f)	$R_{\theta JL}$	139	°C/W

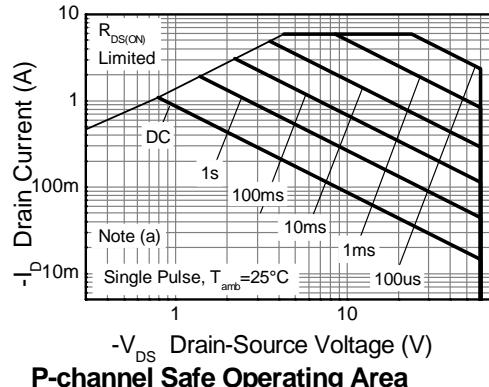
**NOTES:**

- (a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions with the heat-sink split into two equal areas (one for each drain connection); the device is measured when operating in a steady-state condition with one active die.
- (b) Same as note (a), except the device is measured at  $t \leq 10$  sec.
- (c) Same as note (a), except the device is pulsed with  $D = 0.02$  and pulse width 300  $\mu s$ . The pulse current is limited by the maximum junction temperature.
- (d) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions with the heat-sink split into two equal areas (one for each drain connection); the device is measured when operating in a steady-state condition with one active die.
- (e) For a device surface mounted on minimum copper 1.6mm FR4 PCB, in still air conditions; the device is measured when operating in a steady-state condition with one active die.
- (f) Thermal resistance from junction to solder-point (at the end of the drain lead); the device is operating in a steady-state condition with one active die.

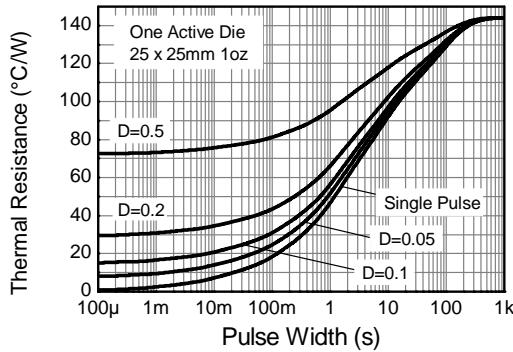
### Thermal characteristics



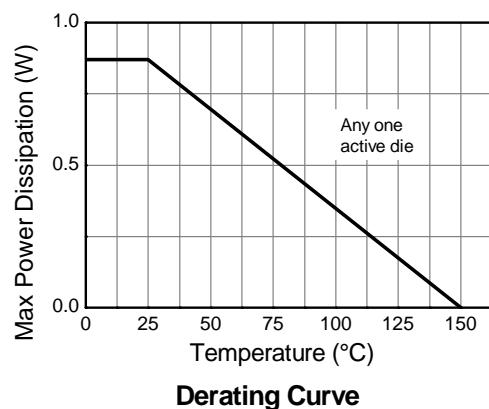
**N-channel Safe Operating Area**



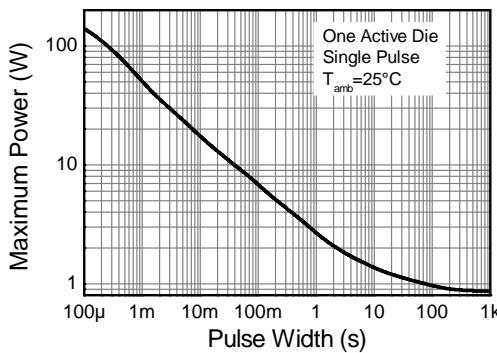
**P-channel Safe Operating Area**



**Transient Thermal Impedance**



**Derating Curve**



**Pulse Power Dissipation**

**N-channel electrical characteristics (at  $T_{amb} = 25^\circ C$  unless otherwise stated)**

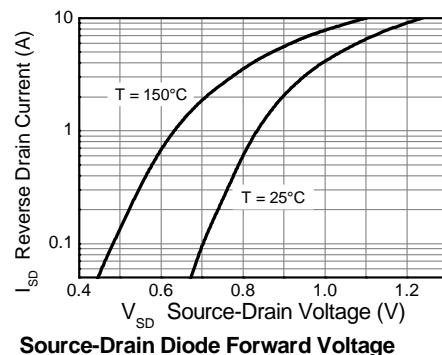
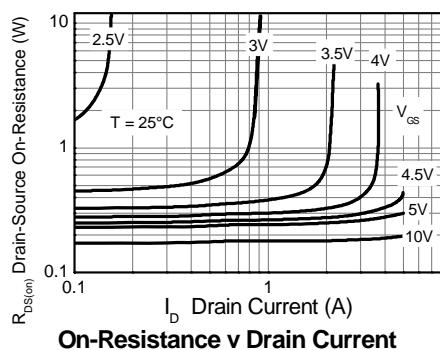
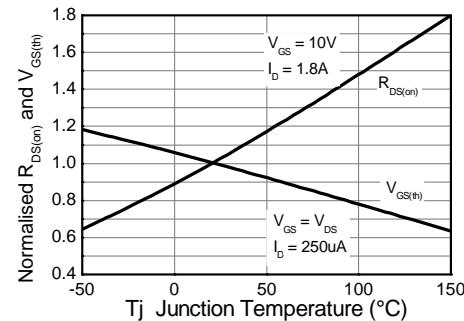
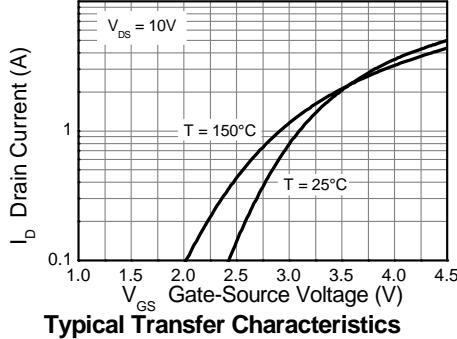
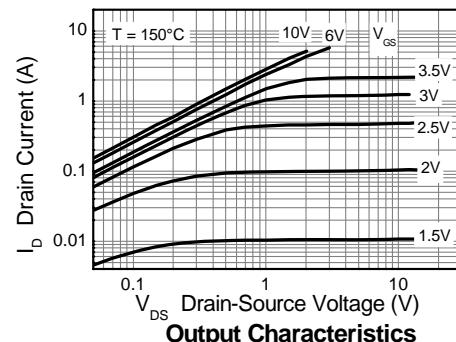
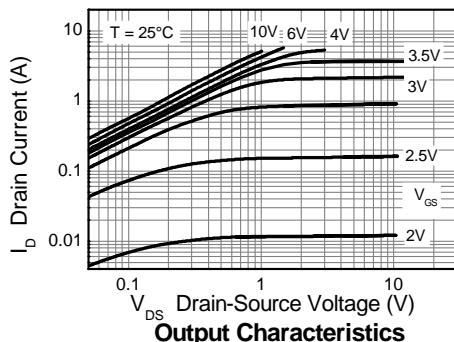
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
<b>Static</b>						
Drain-Source breakdown voltage	$V_{(BR)DSS}$	60			V	$I_D = 250\mu A, V_{GS} = 0V$
Zero Gate voltage Drain current	$I_{DSS}$			0.5	$\mu A$	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body leakage	$I_{GSS}$			$\pm 100$	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Gate-Source threshold voltage	$V_{GS(th)}$	1.0		3.0	V	$I_D = 250\mu A, V_{DS} = V_{GS}$
Static Drain-Source on-state resistance <sup>(a)</sup>	$R_{DS(on)}$			0.25 0.35	$\Omega$	$V_{GS} = 10V, I_D = 1.8A$ $V_{GS} = 4.5V, I_D = 1.3A$
Forward Transconductance <sup>(a) (c)</sup>	$g_{fs}$		2.3		S	$V_{DS} = 15V, I_D = 1.8A$
<b>Dynamic</b>						
<b>Capacitance <sup>(c)</sup></b>						
Input capacitance	$C_{iss}$		166		pF	
Output capacitance	$C_{oss}$		19.5		pF	$V_{DS} = 40V, V_{GS} = 0V$
Reverse transfer capacitance	$C_{rss}$		8.7		pF	$f = 1MHz$
<b>Switching <sup>(b) (c)</sup></b>						
Turn-on-delay time	$t_{d(on)}$		1.8		ns	
Rise time	$t_r$		1.4		ns	$V_{DD} = 30V, V_{GS} = 10V$
Turn-off delay time	$t_{d(off)}$		4.9		ns	$I_D = 1.8A$
Fall time	$t_f$		2.0		ns	$R_G \geq 6.0\Omega$ ,
<b>Gate charge <sup>(c)</sup></b>						
Total Gate charge	$Q_g$		3.2		nC	
Gate-Source charge	$Q_{gs}$		0.67		nC	$V_{DS} = 30V, V_{GS} = 10V$
Gate-Drain charge	$Q_{gd}$		0.82		nC	$I_D = 1.8A$
<b>Source-Drain diode</b>						
Diode forward voltage <sup>(a)</sup>	$V_{SD}$		0.80	0.95	V	$I_S = 0.45A, V_{GS} = 0V$
Reverse recovery time <sup>(c)</sup>	$t_{rr}$		20.5		ns	$I_S = 1.8A, di/dt = 100A/\mu s$
Reverse recovery charge <sup>(c)</sup>	$Q_{rr}$		21.3		nC	

**NOTES:**(a) Measured under pulsed conditions. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

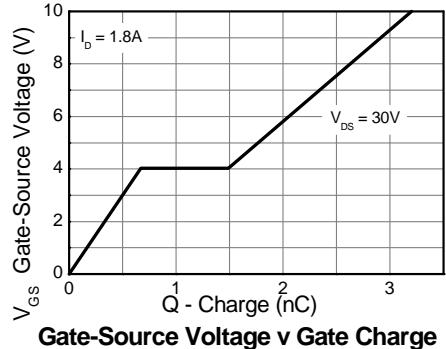
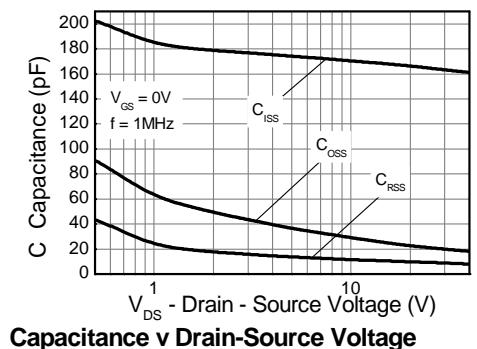
(b) Switching characteristics are independent of operating junction temperature.

(c) For design aid only, not subject to production testing

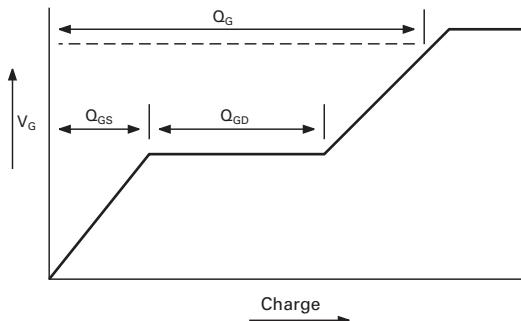
**N-channel typical characteristics**



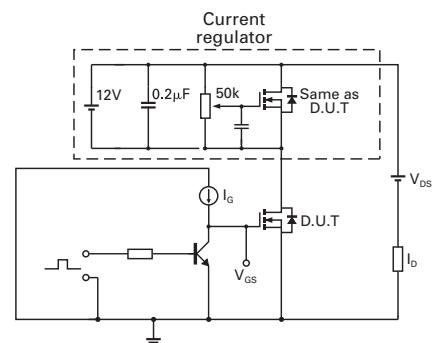
## N-channel typical characteristics –continued



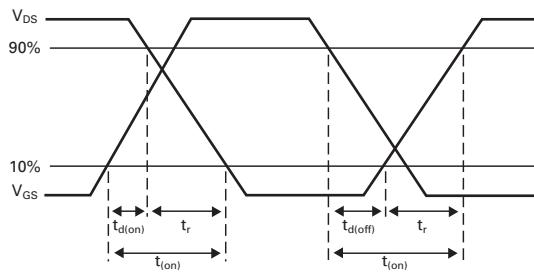
## Test circuits



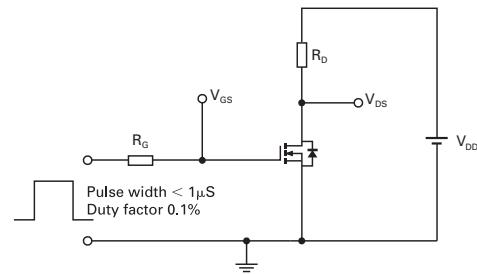
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



Switching time test circuit

**P-channel electrical characteristics (at  $T_{amb} = 25^\circ C$  unless otherwise stated)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
<b>Static</b>						
Drain-Source breakdown voltage	$V_{(BR)DSS}$	-60			V	$I_D = -250\mu A, V_{GS} = 0V$
Zero Gate voltage Drain current	$I_{DSS}$			-0.5	$\mu A$	$V_{DS} = -60V, V_{GS} = 0V$
Gate-Body leakage	$I_{GSS}$			$\pm 100$	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Gate-Source threshold voltage	$V_{GS(th)}$	-1.0		-3.0	V	$I_D = -250\mu A, V_{DS} = V_{GS}$
Static Drain-Source on-state resistance <sup>(a)</sup>	$R_{DS(on)}$			0.40 0.60	$\Omega$	$V_{GS} = -10V, I_D = -0.9A$ $V_{GS} = -4.5V, I_D = -0.8A$
Forward Transconductance <sup>(a) (c)</sup>	$g_{fs}$		1.8		S	$V_{DS} = -15V, I_D = -0.9A$
<b>Dynamic</b>						
<b>Capacitance <sup>(c)</sup></b>						
Input capacitance	$C_{iss}$		141		pF	
Output capacitance	$C_{oss}$		13.1		pF	$V_{DS} = -50V, V_{GS} = 0V$
Reverse transfer capacitance	$C_{rss}$		10.8		pF	$f = 1MHz$
<b>Switching <sup>(b) (c)</sup></b>						
Turn-on-delay time	$t_{d(on)}$		1.6		ns	
Rise time	$t_r$		2.3		ns	$V_{DD} = -30V, V_{GS} = -10V$
Turn-off delay time	$t_{d(off)}$		13		ns	$I_D = -1.0A$
Fall time	$t_f$		5.8		ns	$R_G \geq 6.0\Omega$
<b>Gate charge <sup>(c)</sup></b>						
Total Gate charge	$Q_g$		5.1		nC	
Gate-Source charge	$Q_{gs}$		0.7		nC	$V_{DS} = -30V, V_{GS} = -10V$
Gate-Drain charge	$Q_{gd}$		0.7		nC	$I_D = -0.9A$
<b>Source-Drain diode</b>						
Diode forward voltage <sup>(a)</sup>	$V_{SD}$		-0.85	-0.95	V	$I_S = -0.8A, V_{GS} = 0V$
Reverse recovery time <sup>(c)</sup>	$t_{rr}$		22.6		ns	$I_S = -0.9A, di/dt = 100A/\mu s$
Reverse recovery charge <sup>(c)</sup>	$Q_{rr}$		23.2		nC	

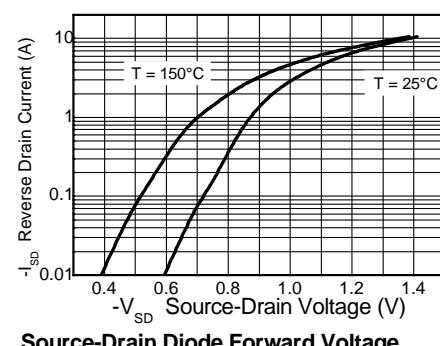
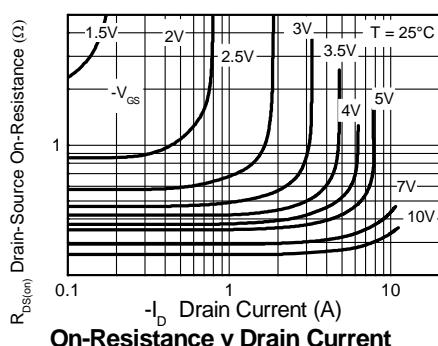
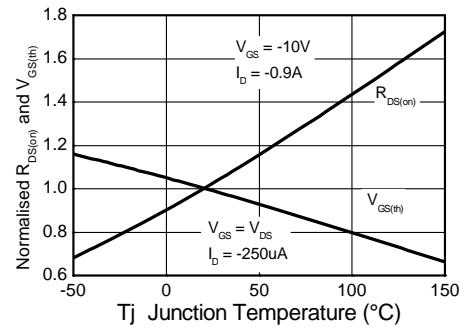
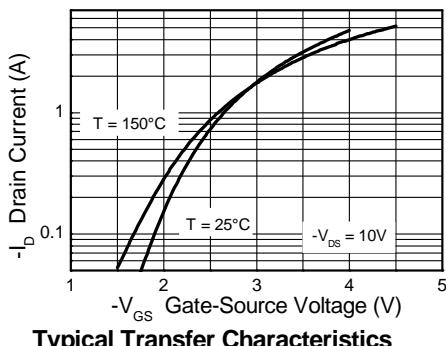
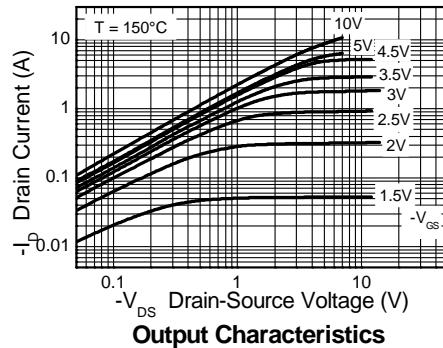
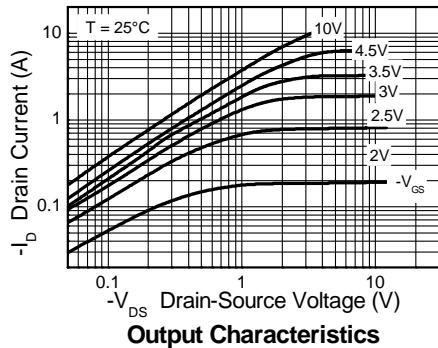
**NOTES:**

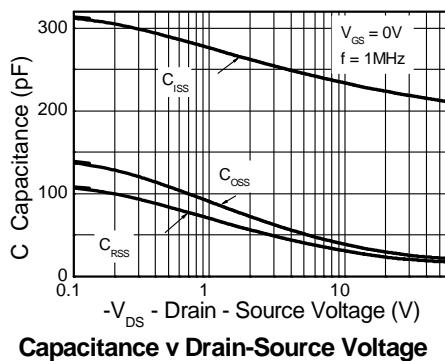
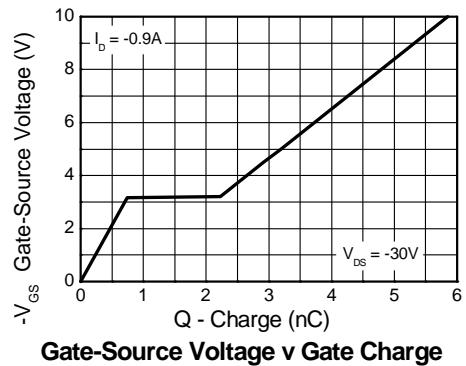
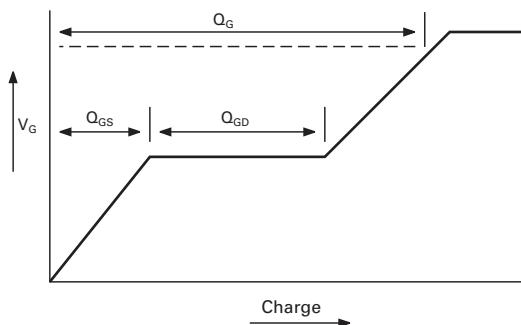
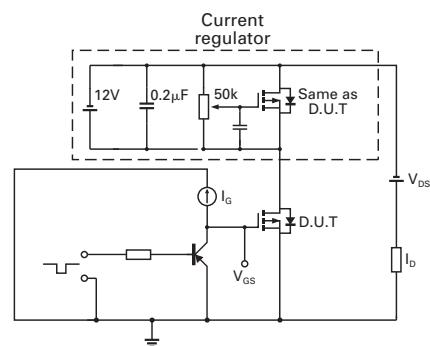
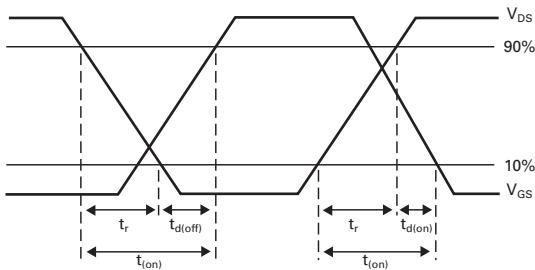
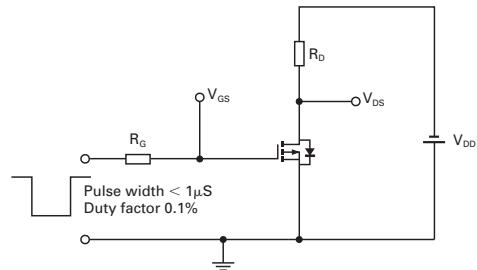
(a) Measured under pulsed conditions. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

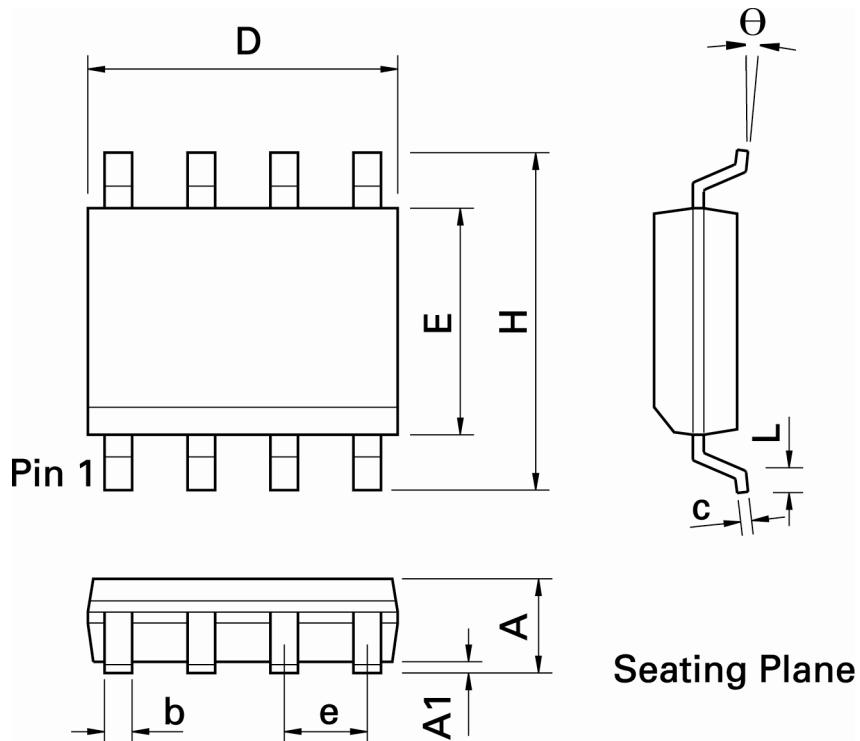
(b) Switching characteristics are independent of operating junction temperature.

(c) For design aid only, not subject to production testing

**P-channel typical characteristics**



**P-channel typical characteristics –continued**

**Capacitance v Drain-Source Voltage**

**Gate-Source Voltage v Gate Charge**
**Test circuits**

**Basic gate charge waveform**

**Gate charge test circuit**

**Switching time waveforms**

**Switching time test circuit**

**Packaging details - SO8**

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	θ	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	-	-	-	-	-
L	0.016	0.050	0.40	1.27	-	-	-	-	-

**Note:** Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

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